IN THE CLAIMS:

Please cancel claims 1-21 without prejudice and add new claims 22-38 as shown in the following list of claims:

1-21. (Cancelled)

22. (New) A method for processing a substrate, comprising:

depositing an electrically conductive seed layer onto a substrate;

immersing the substrate into a plating solution; and

plating metal ions from the plating solution onto the substrate during the

immersing process by applying a plating bias to the substrate at a charge density

between about 20 mA*sec/cm² and about 160 mA*sec/cm².

- 22. (New) The method of claim 22, wherein applying a plating bias to the substrate comprises applying a bias between about 0.8 volts and about 20 volts for a period of time sufficient to compensate for etching of the seed layer by the plating solution during the immersing process.
- 23. (New) The method of claim 23, wherein the plating bias is applied between about 0.1 seconds and about 4 seconds.
- 24. (New) The method of claim 22, wherein plating metal ions from the plating solution comprises plating a layer of metal ions onto the seed layer, wherein the layer of metal ions has a thickness of between about 50Å and about 250Å.
- 25. (New) The method of claim 22, wherein the metal ions comprise at least one of copper, nickel, and tungsten.
- 26. (New) The method of claim 22, wherein the applying the plating bias comprises applying an increasing plating bias to the substrate during the immersing process.

- 27. (New) The method of claim 22, wherein the applying the plating bias comprises applying a pulse modulated plating bias to the substrate during the immersion process.
- 28. (New) The method of claim 22, wherein plating metal ions from the plating solution comprises plating an alloy layer onto the seed layer.
- 29. (New) A method for electrochemically plating a first metal layer onto a substrate surface having high aspect ratio features formed thereon, comprising:

depositing a seed layer over the substrate surface and features;

immersing the substrate surface and features into an electrochemical plating solution; and

applying a plating bias at a charge density of between about 20 mA*sec/cm² and about 160 mA*sec/cm² during the immersing process to deposit a first metal layer on the seed layer.

- 30. (New) The method of claim 29, wherein applying the plating bias comprises applying an increasing plating bias to the substrate during the immersing process or applying a pulse modulated plating bias to the substrate during the immersion process.
- 31. (New) The method of claim 29, wherein the plating bias is applied for a duration of between about 0.5 seconds and about 2 seconds.
- 32. (New) The method of claim 29, wherein applying the plating bias comprises applying a bias between about 0.8 volts and about 20 volts to the seed layer for a period of time between about 0.1 second and about 4.0 seconds during the immersing process.
- 33. (New) The method of claim 29, further comprising plating a second metal layer over the first metal layer via an electrochemical plating process after the seed layer is fully immersed in the electrochemical plating solution.

- 34. (New) The method of claim 29, wherein the first layer is a metal alloy layer.
- 35. (New) A method for immersing a substrate into a plating solution, comprising immersing the substrate into the plating solution while simultaneously applying a charge density of between about 20 mA*sec/cm² and about 160 mA*sec/cm².
- 36. (New) The method of claim 35, wherein the charge density is applied by applying a plating bias between about 0.8 volts and about 20 volts to the substrate for a period of between about 0.1 seconds and about 4 seconds.
- 37. (New) The method of claim 35, wherein the plating bias causes the deposition of a patching layer over a seed layer formed onto the substrate during the immersing process.
- 38. (New) The method of claim 37, wherein the patching layer comprises a metal alloy layer.